



# BUK6Y61-60P

60 V, P-channel Trench MOSFET

13 March 2026

Product data sheet

## 1. General description

P-channel enhancement mode MOSFET in an LFPAK56 (Power SO8) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

This product has been designed and qualified to AEC-Q101 standard for use in high-performance automotive applications such as reverse battery protection.

## 2. Features and benefits

- High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating
- Trench MOSFET technology
- AEC-Q101 qualified

## 3. Applications

- Reverse battery protection
- Power management
- High-side load switch
- Motor drive

## 4. Quick reference data

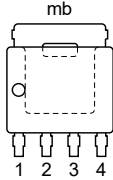
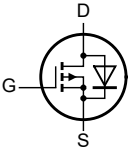
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-60	V
$V_{GS}$	gate-source voltage	[1]	-20	-	20	V
$I_D$	drain current	$V_{GS} = -10\text{ V}; T_{mb} = 25\text{ °C}$	-	-	-25	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$	-	-	66	W
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -10\text{ V}; I_D = -4.7\text{ A}; T_j = 25\text{ °C}$	-	48	61	mΩ

[1]  $V_{GS} = -20\text{ V}/+5\text{ V}$  according AEC-Q101 at  $T_j = 175\text{ °C}$ ;  $V_{GS} = -20\text{ V}/+20\text{ V}$  according AEC-Q101 at  $T_j = 150\text{ °C}$

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p><b>LFPAK56; Power-SO8 (SOT669)</b></p>	 <p>017aaa094</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6Y61-60P	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK6Y61-60P	6Y6160P

## 8. Limiting values

**Table 5. Limiting values**

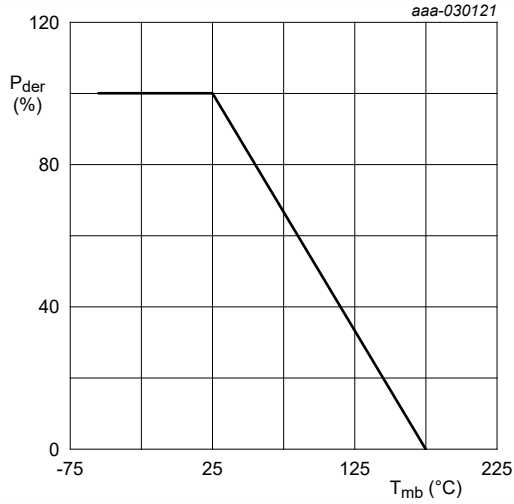
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$		-	-60	V
$V_{GS}$	gate-source voltage		[1]	-20	20	V
$I_D$	drain current	$V_{GS} = -10\text{ V}; T_{mb} = 25\text{ }^\circ\text{C}$		-	-25	A
		$V_{GS} = -10\text{ V}; T_{mb} = 100\text{ }^\circ\text{C}$		-	-17.7	A
$I_{DM}$	peak drain current	single pulse; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ }^\circ\text{C}$		-	-100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$		-	66	W
$T_j$	junction temperature			-55	175	$^\circ\text{C}$
$T_{amb}$	ambient temperature			-55	175	$^\circ\text{C}$
$T_{stg}$	storage temperature			-65	175	$^\circ\text{C}$
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ }^\circ\text{C}$		-	-25	A
$I_{SM}$	peak source current	single pulse; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ }^\circ\text{C}$		-	-100	A
<b>ESD maximum rating</b>						
$V_{ESD}$	electrostatic discharge voltage	HBM	[2]	-	800	V
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{sup} \leq -30\text{ V}; V_{GS} = -10\text{ V}; T_{j(\text{init})} = 25\text{ }^\circ\text{C}; R_{GS} = 50\text{ }\Omega; I_D = -19.5\text{ A}; \text{ unclamped}$	[3]	-	36	mJ
		$V_{sup} \leq -30\text{ V}; V_{GS} = -10\text{ V}; T_{j(\text{init})} = 25\text{ }^\circ\text{C}; R_{GS} = 50\text{ }\Omega; I_D = -4.6\text{ A}$	[3]	-	142	mJ
$I_{AS}$	non-repetitive avalanche current	$T_{j(\text{init})} = 25\text{ }^\circ\text{C}$	[3]	-	19.5	A

[1]  $V_{GS} = -20\text{ V}/+5\text{ V}$  according AEC-Q101 at  $T_j = 175\text{ }^\circ\text{C}$ ;  $V_{GS} = -20\text{ V}/+20\text{ V}$  according AEC-Q101 at  $T_j = 150\text{ }^\circ\text{C}$

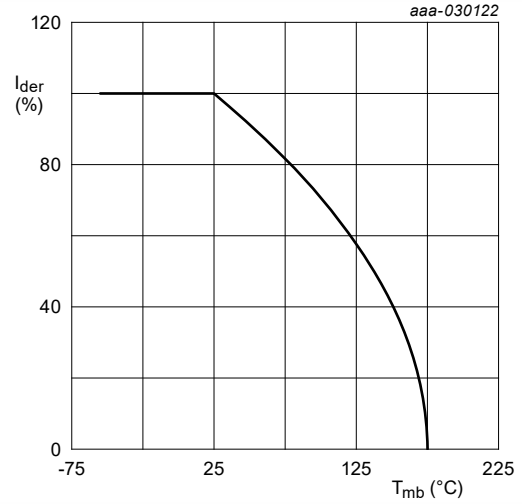
[2] Measured between all pins.

[3] Protected by 100% test.



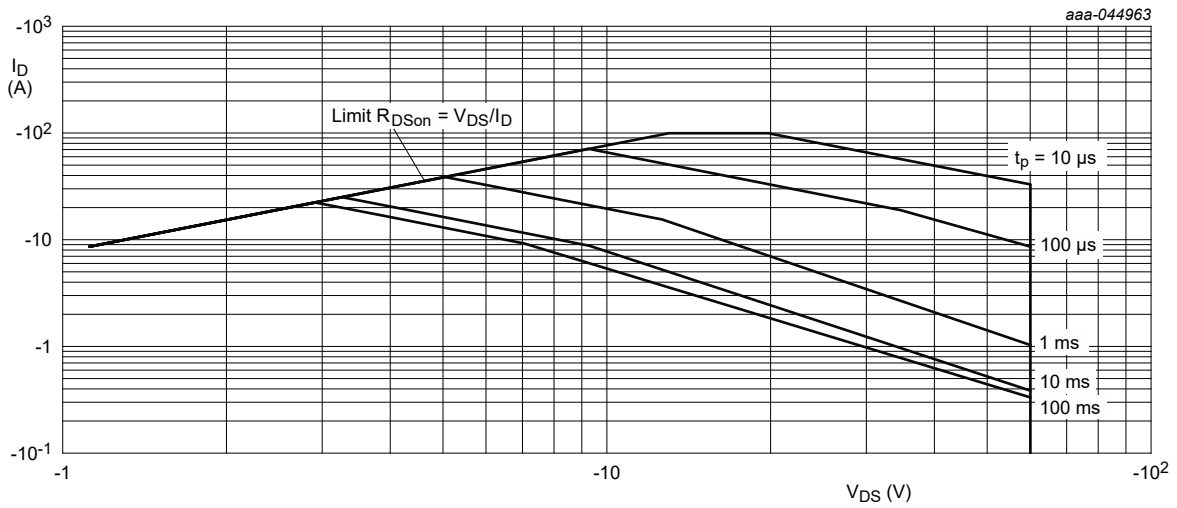
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

**Fig. 2. Normalized continuous drain current as a function of mounting base temperature**



**Fig. 3. Safe operating area; junction to mounting base; continuous and peak drain currents as a function of drain-source voltage**

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	1.8	2.3	K/W

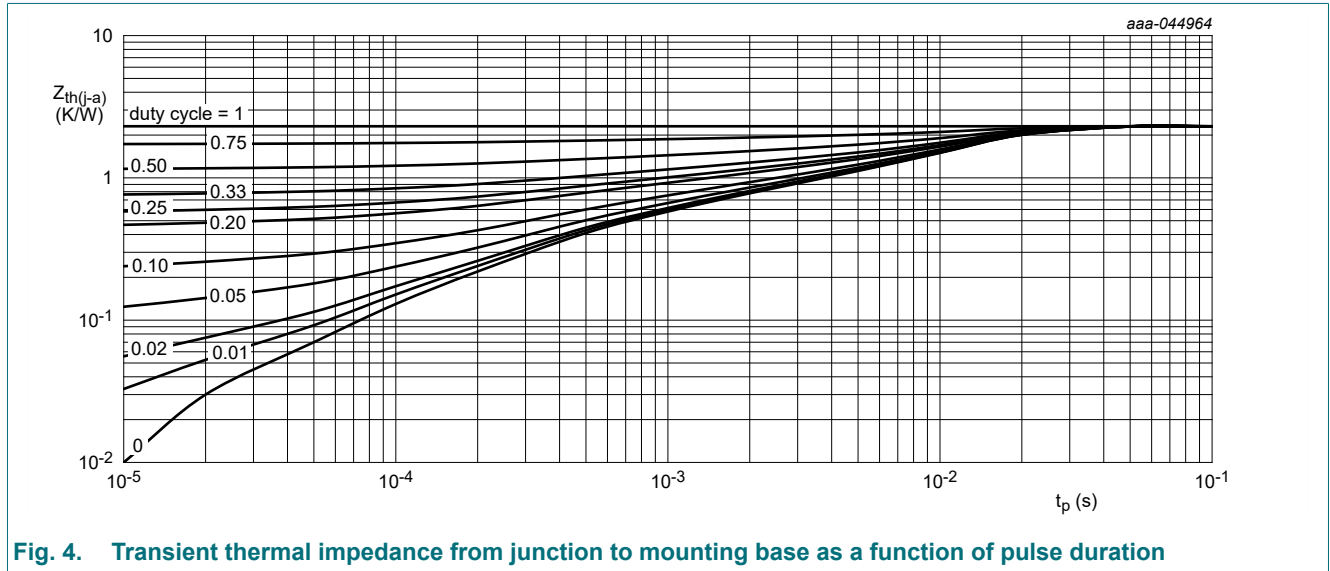


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu\text{A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu\text{A}$ ; $V_{DS}=V_{GS}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-1.5	-2	-3	V
$I_{DSS}$	drain leakage current	$V_{DS} = -60 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	-1	$\mu\text{A}$
		$V_{DS} = -60 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 125 \text{ }^\circ\text{C}$	-	-	-10	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = -20 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	-100	nA
		$V_{GS} = 20 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -10 \text{ V}$ ; $I_D = -4.7 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	48	61	m $\Omega$
		$V_{GS} = -10 \text{ V}$ ; $I_D = -4.7 \text{ A}$ ; $T_j = 175 \text{ }^\circ\text{C}$	-	100	130	m $\Omega$
		$V_{GS} = -4.5 \text{ V}$ ; $I_D = -3.8 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	62	93	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = -10 \text{ V}$ ; $I_D = -4 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	65	-	S
$R_G$	gate resistance	$f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	12	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -30 \text{ V}$ ; $I_D = -4.7 \text{ A}$ ; $V_{GS} = -10 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	20	30	nC
$Q_{GS}$	gate-source charge		-	3.3	-	nC
$Q_{GD}$	gate-drain charge		-	4.3	-	nC
$C_{iss}$	input capacitance	$V_{DS} = -30 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	1060	-	pF
$C_{oss}$	output capacitance		-	85	-	pF
$C_{rss}$	reverse transfer capacitance		-	49	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -30 \text{ V}$ ; $I_D = -7 \text{ A}$ ; $V_{GS} = -10 \text{ V}$ ; $R_{G(ext)} = 6 \text{ } \Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	3	-	ns
$t_r$	rise time		-	6	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
$t_f$	fall time		-	144	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = -5 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-0.8	-1.2	V
$t_{rr}$	reverse recovery time	$I_S = -5 \text{ A}$ ; $di_S/dt = 100 \text{ A}/\mu\text{s}$ ; $V_{GS} = -10 \text{ V}$ ; $V_{DS} = -30 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	27	-	ns
$Q_r$	recovered charge		-	29	-	nC

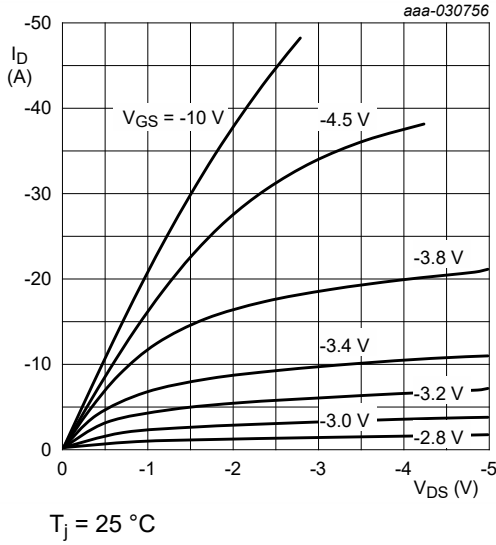


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

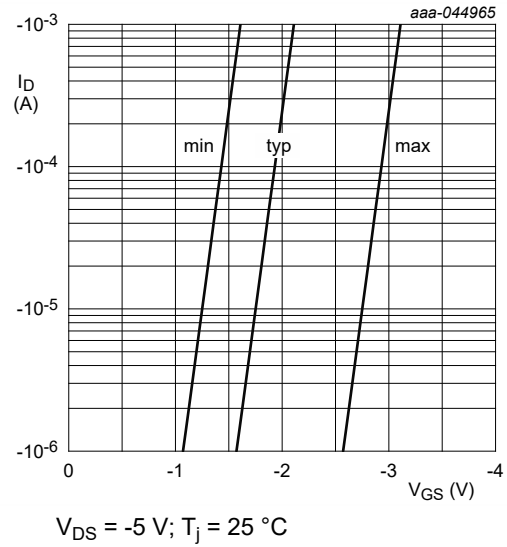


Fig. 6. Sub-threshold drain current as a function of gate-source voltage

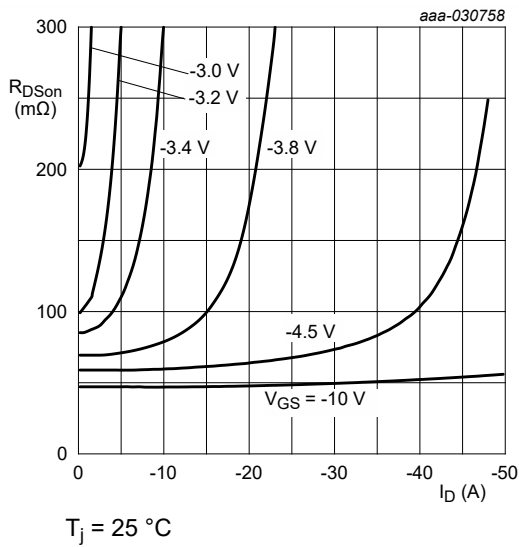


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

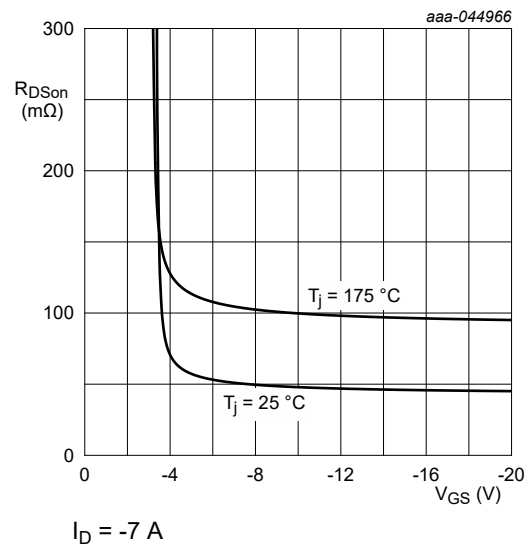


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

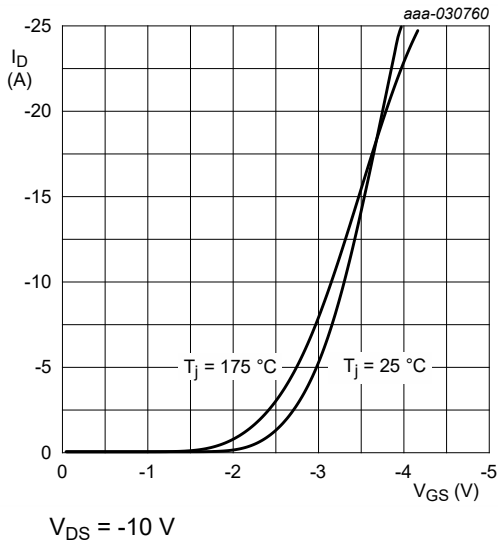
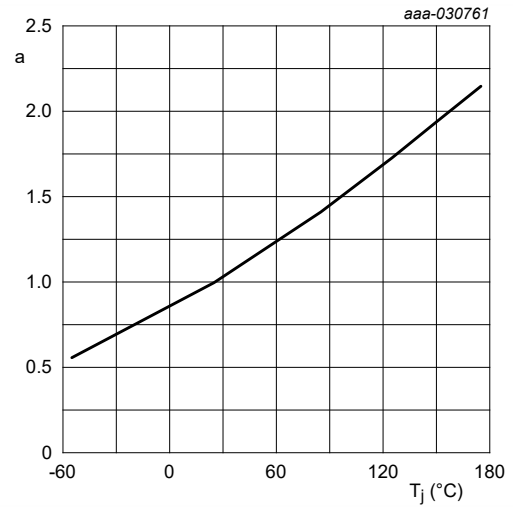
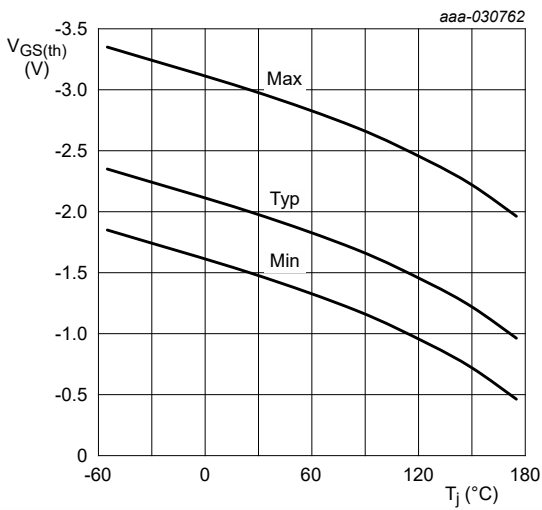


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



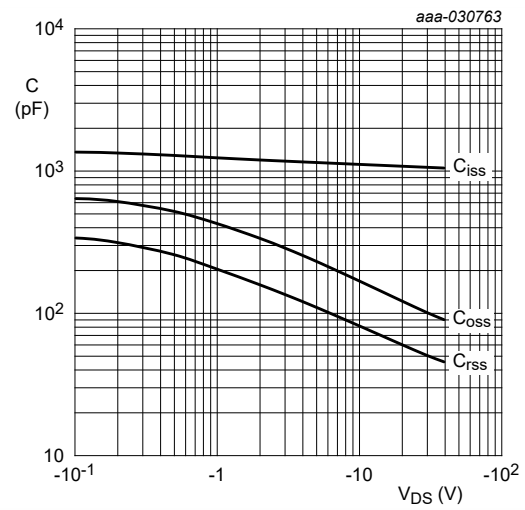
$$a = \frac{R_{DSon}}{R_{DSon(25\text{ °C})}}$$

Fig. 10. Normalized drain-source on-state resistance as a function of junction temperature; typical values



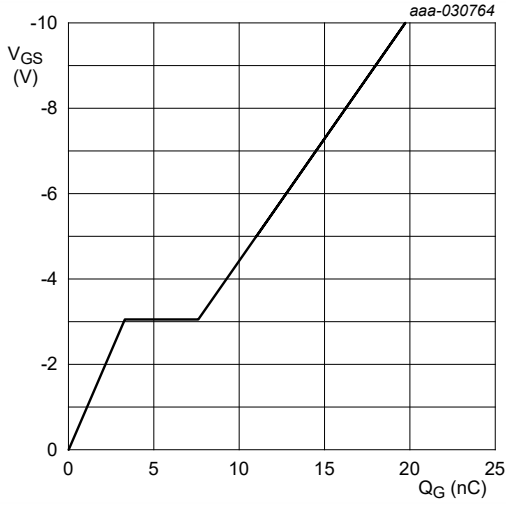
$I_D = -250\text{ }\mu\text{A}$ ;  $V_{DS} = V_{GS}$

Fig. 11. Gate-source threshold voltage as a function of junction temperature



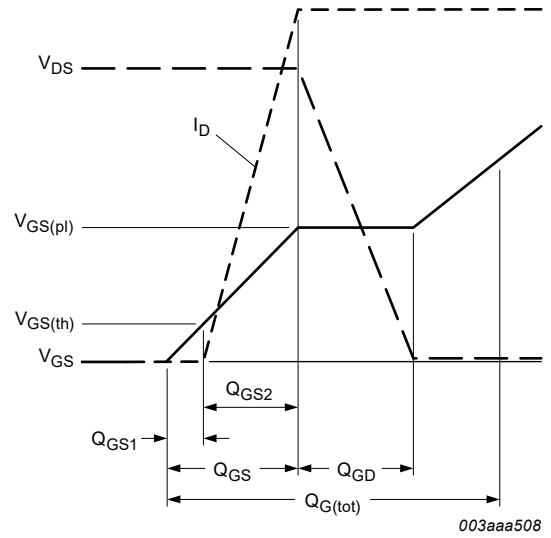
$f = 1\text{ MHz}$ ;  $V_{GS} = 0\text{ V}$

Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

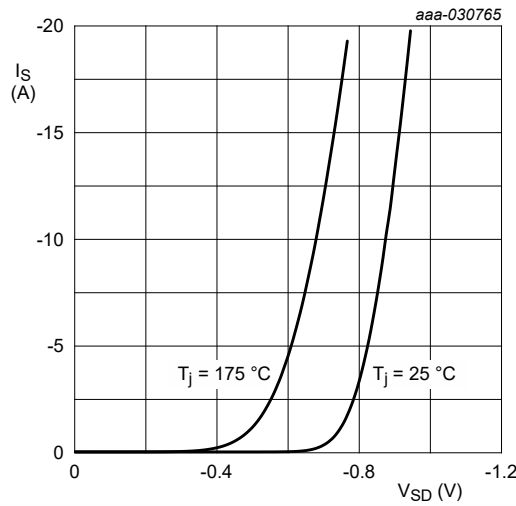


$V_{DS} = -30\text{ V}$ ;  $I_D = -4.8\text{ A}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 13. Gate-source voltage as a function of gate charge; typical values**



**Fig. 14. Gate charge waveform definitions**



$V_{GS} = 0\text{ V}$

**Fig. 15. Source current as a function of source-drain voltage; typical values**

## 11. Test information

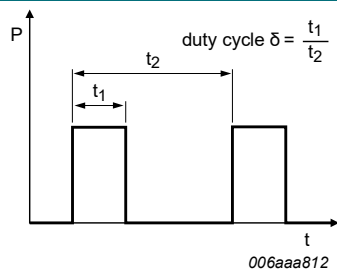


Fig. 16. Duty cycle definition

### Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline

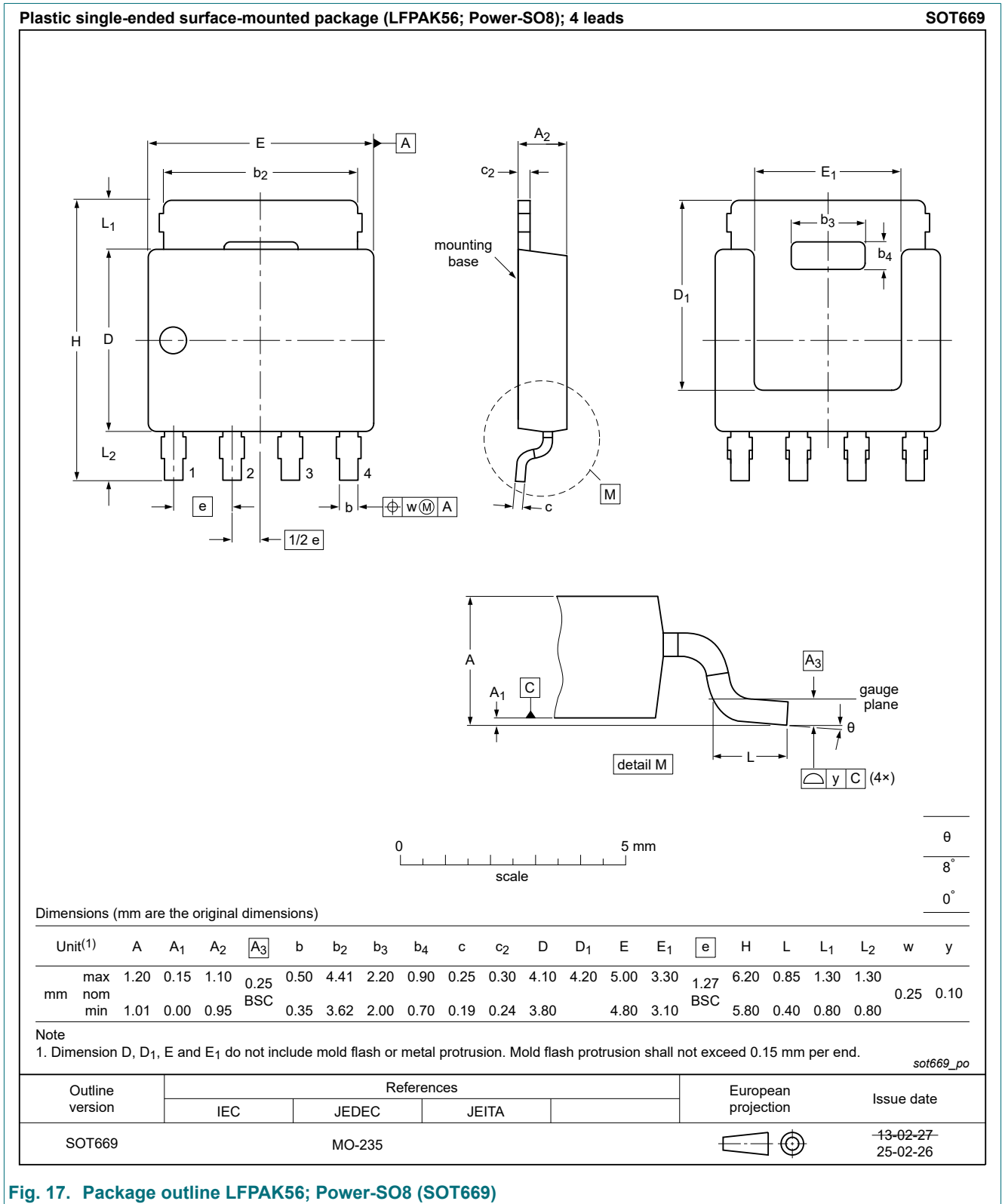


Fig. 17. Package outline LFAK56; Power-SO8 (SOT669)

### 13. Soldering

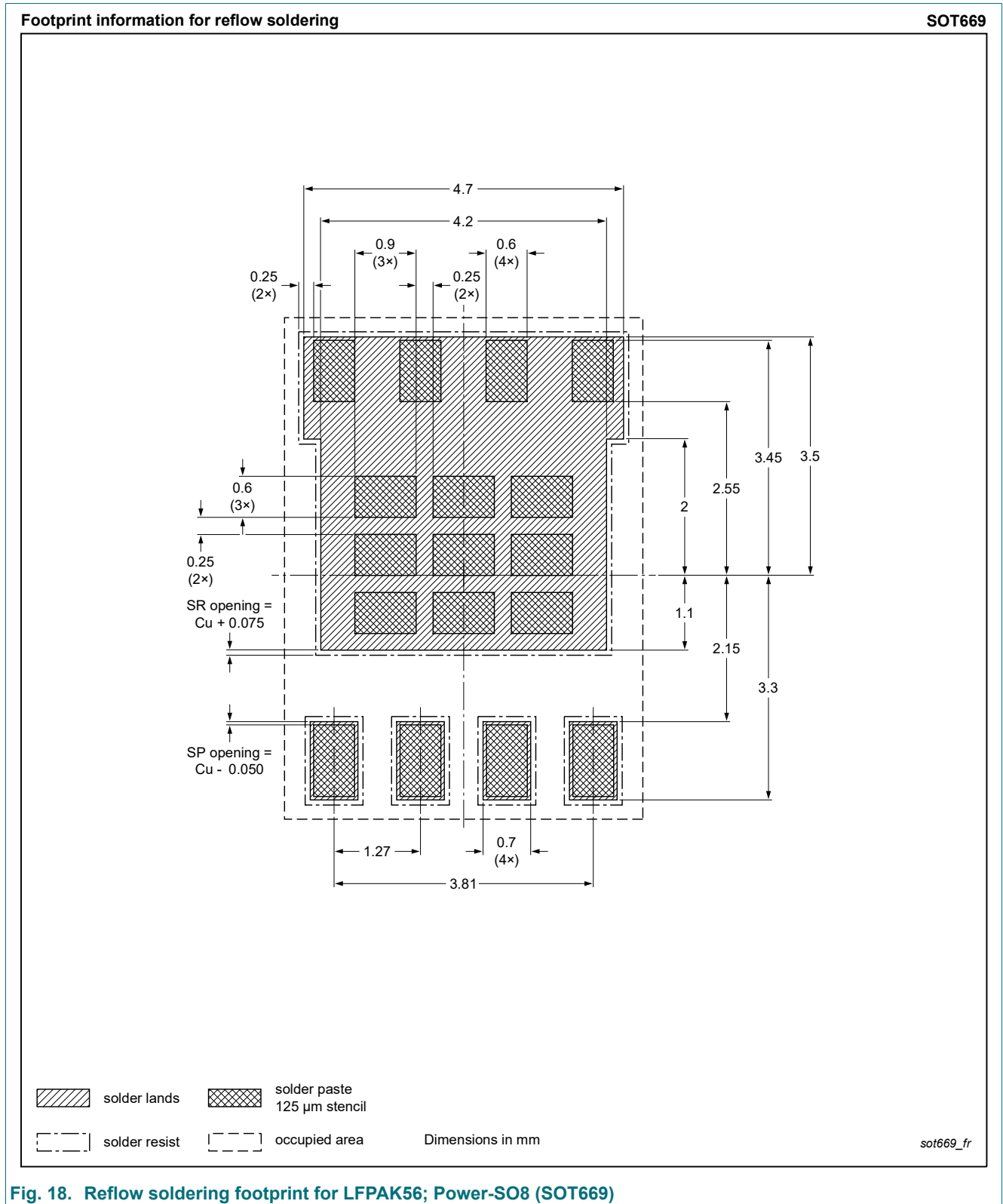


Fig. 18. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

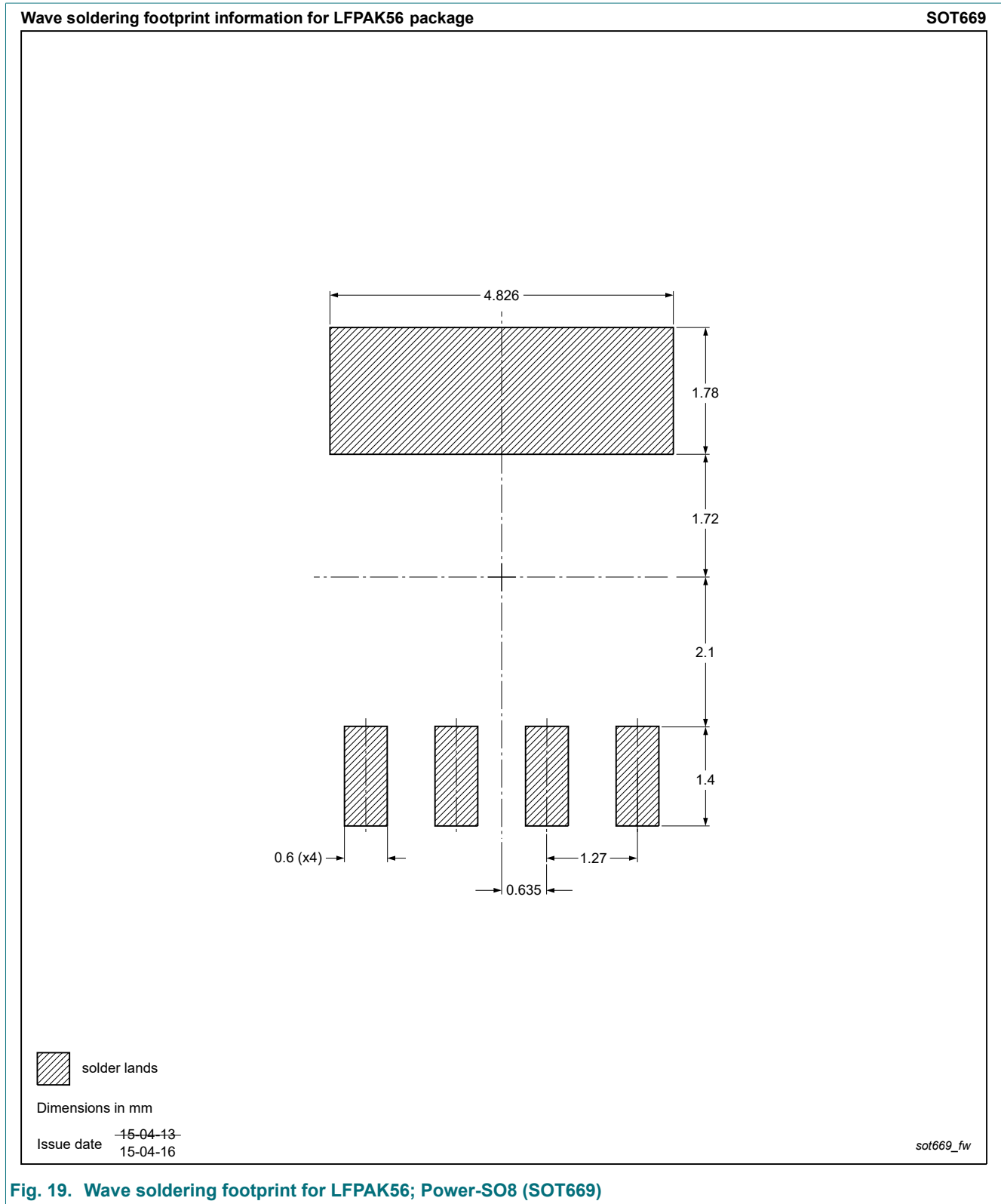


Fig. 19. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BUK6Y61-60P v.2	20260313	Product data sheet	-	BUK6Y61-60P v.1
Modifications:	• Complete rework.			
BUK6Y61-60P v.1	20200316	Product data sheet	-	-

## 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 13 March 2026

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